Unit in mm

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

## **HN3C14FU**

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

2.1±0.1

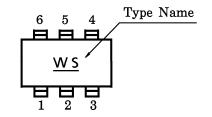
 Including Two Devices in US6 (Ultra Super Mini Type with 6 Leads)

## MAXIMUM RATINGS (Ta = 25°C)

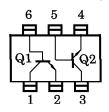
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$v_{\mathrm{CBO}}$	20	V
Collector-Emitter Voltage	$V_{CEO}$	10	V
Emitter-Base Voltage	$V_{EBO}$	3	V
Collector Current	$I_{\mathbf{C}}$	60	mA
Base Current	$I_{B}$	30	mA
Collector Power Dissipation	PC*	200	mW
Junction Temperature	$T_{j}$	125	°C
Storage Temperature Range	T <sub>stg</sub>	-55~125	°C

\*: Total

**MARKING** 



PIN ASSIGNMENT (TOP VIEW)



2.0±0.2 1.3±0.1 1.3±0.1 1.3±0.1 1.0				
1. COLLECTOR 1 (C1) 2. EMITTER 1 (E1) 3. COLLECTOR 2 (C2) 4. EMITTER 2 (E2) 5. BASE 2 (B2) 6. BASE 1 (B1)				
JEDEC —				
EIAJ —				
TOSHIBA 2-2J1A				

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=10V, I_{E}=0$	_	_	1	μA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=1V, I_{C}=0$	_	_	1	$\mu$ A
DC Current Gain	$\mathbf{h_{FE}}$	$V_{CE}=5V, I_{C}=5mA$	80	_	240	_
Transition Frequency	$ m f_{T}$	$V_{CE}=5V, I_{C}=5mA$	3	5	_	GHz
Insertion Gain	$ \mathrm{S}_{21\mathrm{e}} ^2$	$V_{CE}$ =5V, $I_{C}$ =5mA, f=1GHz	6	10	<u> </u>	dB
Reverse Transfer Capacitance Q1	$\mathrm{C_{re}}$	V <sub>CB</sub> =5V, I <sub>E</sub> =0, f=1MHz (Note)	_	0.9	_	pF
Reverse Transfer Capacitance Q2	$C_{re}$		_	0.7	1.1	pF

(Note) Cre is measured by 3 terminal method capacitance bridge.

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